EMX1DXV6T1G, EMX1DXV6T5G

Dual NPN General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-563 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE}, 210–460 (Typical)
- Low V_{CE(sat)}, < 0.5 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	7.0	Vdc
Collector Current – Continuous	Ι _C	100	mAdc

THERMAL CHARACTERISTICS Characteristic (One Junction Heated) Symbol Unit Max **Total Device Dissipation** P_{D} $T_A = 25^{\circ}C$ 357 (Note 1) mW Derate above 25°C 2.9 (Note 1) mW/°C

Thermal Resistance – Junction-to-Ambient	R_{\thetaJA}	350 (Note 1)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Мах	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	500 (Note 1) 4.0 (Note 1)	mW mW/°C
Thermal Resistance – Junction-to-Ambient	R_{\thetaJA}	250 (Note 1)	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

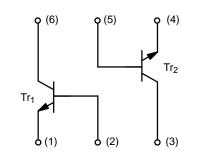
1. FR-4 @ Minimum Pad



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DUAL NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT





CASE 463A STYLE 1

MARKING DIAGRAM



3X = Specific Device Code M = Month Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

EMX1DXV6T1G, EMX1DXV6T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage $(I_C = 50 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	60	-	-	Vdc
Collector-Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	50	-	_	Vdc
Emitter-Base Breakdown Voltage $(I_E = 50 \ \mu Adc, I_E = 0)$	V _{(BR)EBO}	7.0	-	_	Vdc
Collector-Base Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_E = 0$)	Ісво	-	-	0.5	μΑ
Emitter-Base Cutoff Current ($V_{EB} = 7.0 \text{ Vdc}, I_B = 0$)	I _{EBO}	-	-	0.5	μΑ
Collector-Emitter Saturation Voltage (Note 2) $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{CE(sat)}	-	_	0.4	Vdc
DC Current Gain (Note 3) ($V_{CE} = 6.0$ Vdc, $I_C = 1.0$ mAdc)	h _{FE}	120	-	560	-
Transition Frequency (V_{CE} = 12 Vdc, I _C = 2.0 mAdc, f = 30 MHz)	fT	-	180	-	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_C = 0 Adc, f = 1 MHz)	C _{OB}	-	2.0	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

3. Pulse Test: Pulse Width \leq 300 µs, D.C. \leq 2%.

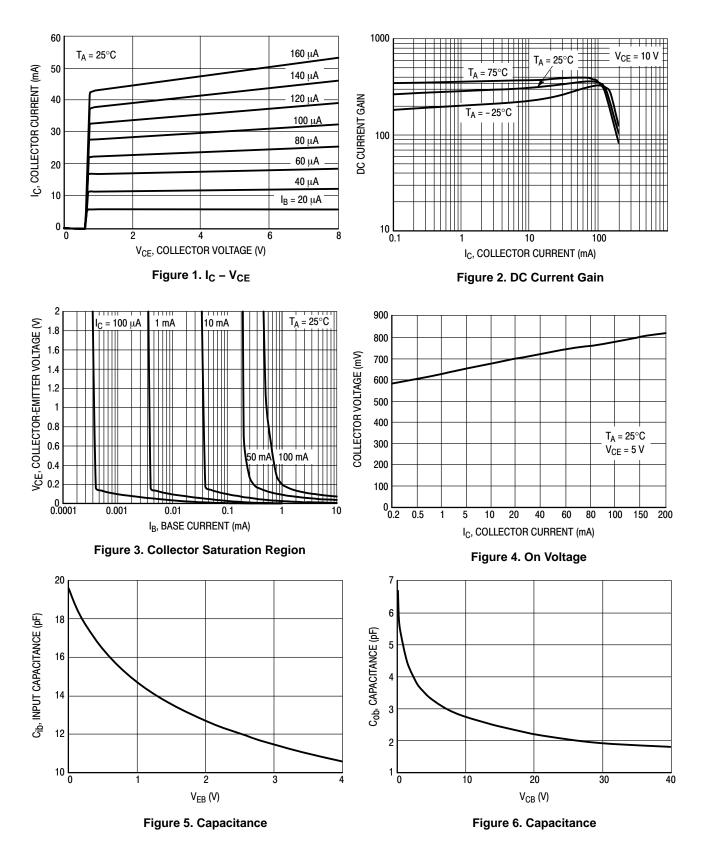
ORDERING INFORMATION

Device	Package	Shipping [†]
EMX1DXV6T1G	SOT–563 (Pb–Free)	4000 Units / Tape & Reel
EMX1DXV6T5G	SOT–563 (Pb–Free)	8000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

EMX1DXV6T1G, EMX1DXV6T5G

TYPICAL ELECTRICAL CHARACTERISTICS



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MILLIMETERS

NDM.

0.55

0.22

0.13

1.60

1.20

0.50 BSC

0.20

1.60

MAX.

0.60

0.27

0.18

1.70

1.30

0.30

1.70

SIDE VIEW

MIN.

0.50

0.17

0.08

1.50

1.10

0.10

1.50

DIM

Α

b

С

D E

e L

 H_E



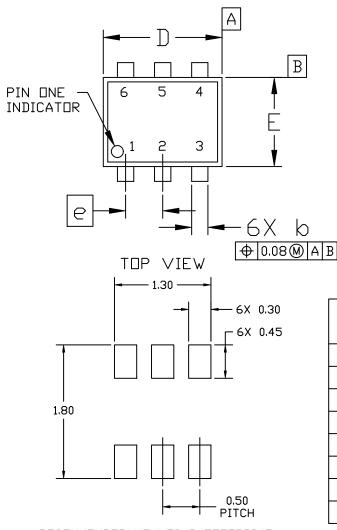


SOT-563, 6 LEAD CASE 463A ISSUE H

DATE 26 JAN 2021

ALE 4:1

- NDTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 1. DIMENSIONING AND TOLERANCING PER A 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF BASE MATERIAL.



RECOMMENDED MOUNTING FOOTPRINT* * For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHIDE 1
2. BASE 1	2. EMITTER 2	2. CATHIDE 1
3. COLLECTOR 2	3. BASE 2	3. ANUDE/ANUDE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHIDE 2
5. BASE 2	5. BASE 1	5. CATHIDE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANUDE/ANUDE 1
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. COLLECTOR	PIN 1. CATHEDE	PIN 1. CATHODE
2. COLLECTOR	2. CATHEDE	2. ANODE
3. BASE	3. ANEDE	3. CATHODE
4. EMITTER	4. ANEDE	4. CATHODE
5. COLLECTOR	5. CATHEDE	5. CATHODE
6. COLLECTOR	6. CATHEDE	6. CATHODE
STYLE 7:	STYLE 8:	STYLE 9:
PIN 1. CATHODE	PIN 1. DRAIN	PIN 1. SDURCE 1
2. ANODE	2. DRAIN	2. GATE 1
3. CATHODE	3. GATE	3. DRAIN 2
4. CATHODE	4. SDURCE	4. SDURCE 2
5. ANODE	5. DRAIN	5. GATE 2
6. CATHODE	6. DRAIN	6. DRAIN 1
STYLE 10: PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1	STYLE 11: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	

6. COLLECTOR 2

DATE 26 JAN 2021

GENERIC **MARKING DIAGRAM***



XX = Specific Device Code

M = Month Code

. = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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PUBLICATION ORDERING INFORMATION

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